

Abstract Submitted  
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**The Ni and Co substitutions in iron chalcogenide single crystals<sup>1</sup>**

V.L. BEZUSYY, D.J. GAWRYLUK, A. MALINOWSKI, M. BERKOWSKI, MARTA Z. CIEPLAK, Institute of Physics PAS, Warsaw — We study the *ab*-plane resistivity and Hall effect in  $\text{Fe}_{1-y}\text{M}_y\text{Te}_{0.65}\text{Se}_{0.35}$  single crystals with  $\text{M}=\text{Co}$  or  $\text{Ni}$ , and  $y$  up to 0.2. The crystals are grown by Bridgman's method. The low-temperature Hall coefficient  $R_H$  changes sign to negative for crystals with  $y$  exceeding 0.135 (Co) and 0.06 (Ni), consistent with the electron doping induced by these impurities. However, the  $R_H$  remains positive for all samples at high  $T$ , suggesting that remnant hole pockets survive the doping, but the holes become localized at low  $T$  in heavily doped crystals. Superconducting transition temperature ( $T_c$ ) approaches zero for  $y = 0.14$  (Co), and 0.03 (Ni), while the resistivity at the  $T_c$  onset is only weakly affected by Co doping, but it increases strongly for the Ni. These results suggest that in case of Co impurity the  $T_c$  suppression may be attributed to electron doping. On the other hand, the Ni substitution, in addition to electron doping, induces strong localization effects at small impurity contents. Using two-band conduction model we argue that the localization of electron carriers is responsible for strong superconductivity suppression by Ni impurity.

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